

# Eronides Felisberto da Silva

## List of Publications by Year in descending order

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18  
papers

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times ranked

314  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of H <sub>2</sub> O <sub>2</sub> in passivation of n- and p-type 4H-SiC surfaces. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 675-678.	1.8	0
2	Electronic and magnetic properties of SnO <sub>2</sub> /CrO <sub>2</sub> thin superlattices. Nanoscale Research Letters, 2011, 6, 146.	5.7	8
3	Study of the vertical transport in p-doped superlattices based on group III-V semiconductors. Nanoscale Research Letters, 2011, 6, 175.	5.7	0
4	Tailoring the Electrical Properties of ZnO/Polyaniline Heterostructures for Device Applications. Journal of the Korean Physical Society, 2011, 58, 1256-1260.	0.7	14
5	Spin-polarization effects in homogeneous and non-homogeneous diluted magnetic semiconductor heterostructures. Nanotechnology, 2010, 21, 375401.	2.6	4
6	Production of Ball-Lightning-Like Luminous Balls by Electrical Discharges in Silicon. Physical Review Letters, 2007, 98, 048501.	7.8	42
7	Nanowire growth on Si wafers by oxygen implantation and annealing. Applied Surface Science, 2006, 252, 5572-5574.	6.1	22
8	Fabrication of high quality silicon-polyaniline heterojunctions. Applied Surface Science, 2002, 190, 390-394.	6.1	45
9	X-Ray Radiation Response of Epitaxial and Nonepitaxial n-6H-SiC Metal-Oxide-Semiconductor Capacitors. Japanese Journal of Applied Physics, 2001, 40, 2987-2990.	1.5	3
10	A novel fluorinated Eu(III) $\beta^2$ -diketone complex as thin film for optical device applications. Optical Materials, 1998, 11, 23-28.	3.6	64
11	Simulation of the early stages of thin film growth. Semiconductor Science and Technology, 1997, 12, 1038-1045.	2.0	12
12	Radiation-induced enhancement of minority-carrier lifetimes in metal/SiO <sub>2</sub> /Si capacitors having oxides grown in O <sub>2</sub> with trichloroethane additive. Applied Physics Letters, 1988, 53, 592-594.	3.3	5
13	Equivalence between interface traps in SiO <sub>2</sub> /Si generated by radiation damage and hot-electron injection. Applied Physics Letters, 1988, 52, 720-722.	3.3	28
14	Time-dependent evolution of SiO <sub>2</sub> /Si interface traps after repeated radiation damage. Journal of Applied Physics, 1988, 64, 3317-3319.	2.5	5
15	Radiation-Induced Interface Traps in Mo/SiO <sub>2</sub> /Si Capacitors. IEEE Transactions on Nuclear Science, 1987, 34, 1166-1171.	2.0	27
16	Effects of trichloroethane during oxide growth on radiation-induced interface traps in Metal/SiO <sub>2</sub> /Si capacitors. Applied Physics Letters, 1987, 51, 1262-1264.	3.3	8
17	Two distinct interface trap peaks in radiation-damaged metal/SiO <sub>2</sub> /Si structures. Applied Physics Letters, 1987, 51, 270-272.	3.3	46
18	Radiation Response of MOS Capacitors Containing Fluorinated Oxides. IEEE Transactions on Nuclear Science, 1987, 34, 1190-1195.	2.0	112